

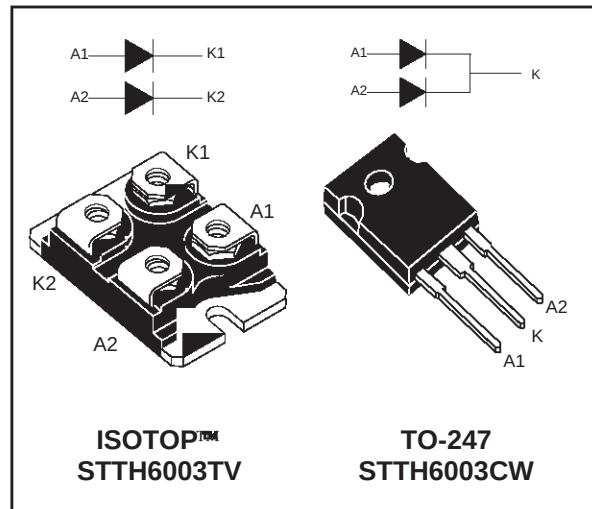
HIGH FREQUENCY SECONDARY RECTIFIER

MAJOR PRODUCT CHARACTERISTICS

$I_F(AV)$	2 x 30 A
V_{RRM}	300 V
$V_F(max)$	1 V
$t_{rr}(max)$	55 ns

FEATURES AND BENEFITS

- COMBINES HIGHEST RECOVERY AND VOLTAGE PERFORMANCE
- ULTRA-FAST, SOFT AND NOISE-FREE RECOVERY
- INSULATED PACKAGE: ISOTOP
Insulation voltage: 2500 V_{RMS}
Capacitance: < 45 pF
- LOW INDUCTANCE AND LOW CAPACITANCE ALLOW SIMPLIFIED LAYOUT



DESCRIPTION

Dual rectifiers suited for Switch Mode Power Supply and high frequency DC to DC converters.

Packaged either in ISOTOP or in TO-247, this device is intended for use in low voltage, high

frequency inverters, free wheeling operation, welding equipments and telecom power supplies.

ABSOLUTE RATINGS (limiting values, per diode)

Symbol	Parameter				Value	Unit
V_{RRM}	Repetitive peak reverse voltage				300	V
$I_F(RMS)$	RMS forward current		ISOTOP		100	A
$I_F(RMS)$	RMS forward current		TO-247		60	A
$I_F(AV)$	Average forward current	ISOTOP	$T_c = 95^\circ C$ $\delta = 0.5$	Per diode Per device	30 60	A
		TO-247	$T_c = 135^\circ C$ $\delta = 0.5$	Per diode Per device	30 60	A
I_{FSM}	Surge non repetitive forward current.	ISOTOP	$t_p = 10$ ms sinusoidal		400	A
		TO-247	$t_p = 10$ ms sinusoidal		300	A
I_{RSM}	Non repetitive peak reverse current		$t_p = 100 \mu s$ square		4	A
T_{stg}	Storage temperature range			ISOTOP	- 55 to + 150	$^\circ C$
				TO-247	- 65 to + 175	$^\circ C$
T_j	Maximum operating junction temperature			ISOTOP	150	$^\circ C$
				TO-247	175	$^\circ C$

THERMAL RESISTANCES

Symbol	Parameter			Value	Unit
$R_{th(j-c)}$	Junction to case	ISOTOP	Per diode Total	1.4 0.75	$^{\circ}\text{C/W}$
		TO-247	Per diode Total	1 0.55	
$R_{th(c)}$	Coupling			0.1	

When the diodes 1 and 2 are used simultaneously:

$$\Delta T_j (\text{diode 1}) = P (\text{diode 1}) \times R_{th(j-c)} (\text{per diode}) + P (\text{diode 2}) \times R_{th(c)}$$

STATIC ELECTRICAL CHARACTERISTICS (per diode)

Symbol	Parameter	Tests conditions		Min.	Typ.	Max.	Unit
I_R^*	Reverse leakage current	$V_R = 300\text{ V}$	$T_j = 25^{\circ}\text{C}$			60	μA
			$T_j = 125^{\circ}\text{C}$		60	600	
V_F^{**}	Forward voltage drop	$I_F = 30\text{ A}$	$T_j = 25^{\circ}\text{C}$			1.25	V
			$T_j = 125^{\circ}\text{C}$		0.85	1	

Pulse test : * $t_p = 5\text{ ms}$, $\delta < 2\%$

** $t_p = 380\text{ }\mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation:

$$P = 0.75 \times I_{F(AV)} + 0.008 \times I_F^2 (RMS)$$

RECOVERY CHARACTERISTICS

Symbol	Tests conditions			Min.	Typ.	Max.	Unit
trr	I _F = 0.5 A	I _{rr} = 0.25 A	I _R = 1A	T _j = 25°C		40	ns
	I _F = 1 A	di _F /dt = - 50 A/μs	V _R = 30 V			55	
tfr	I _F = 30 A di _F /dt = 200 A/μs			T _j = 25°C		350	ns
V _{FP}	V _{FR} = 1.1 x V _F max.					5	
S _{factor}	V _{CC} = 200 V I _F = 30 A			T _j = 125°C		0.3	-
I _{RM}	di _F /dt = 200 A/μs						11

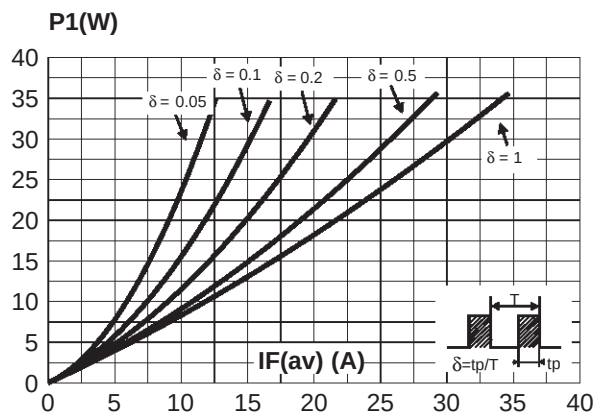
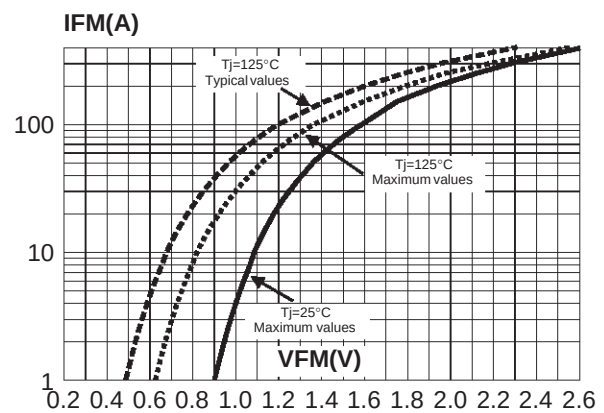
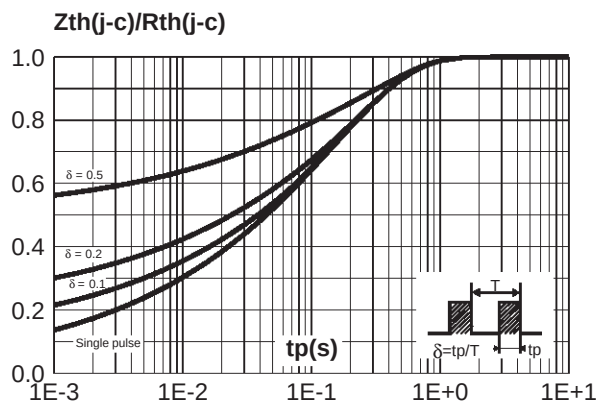
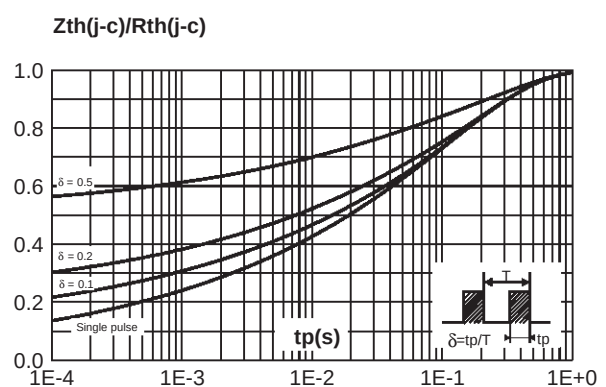
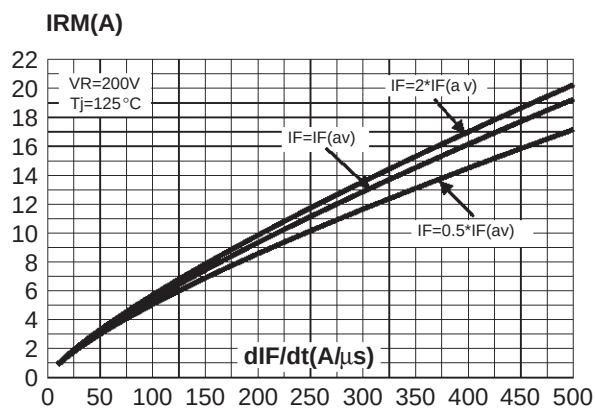
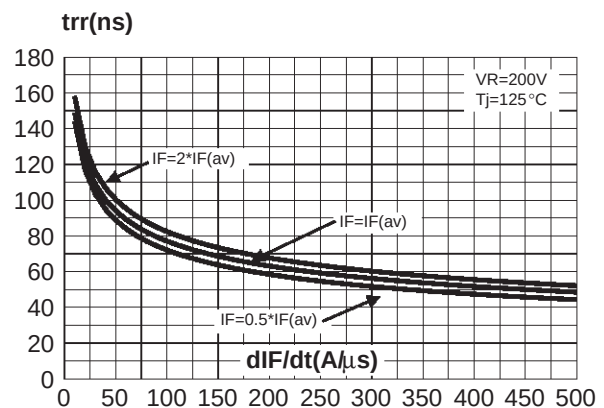
Fig. 1: Conduction losses versus average current (per diode).**Fig. 2:** Forward voltage drop versus forward current (maximum values, per diode).**Fig. 3a:** Relative variation of thermal impedance junction to case versus pulse duration (ISOTOP).**Fig. 3b:** Relative variation of thermal impedance junction to case versus pulse duration (TO-247).**Fig. 4:** Peak reverse recovery current versus dI_F/dt (90% confidence, per diode).**Fig. 5:** Reverse recovery time versus dI_F/dt (90% confidence, per diode).

Fig. 6: Softness factor (tb/ta) versus dI_F/dt (typical values, per diode).

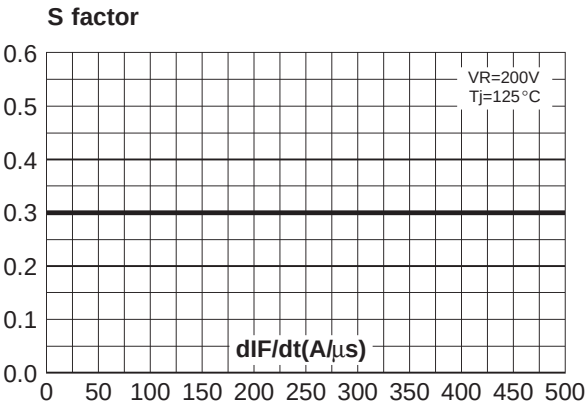


Fig. 7: Relative variation of dynamic parameters versus junction temperature (reference: T_J = 125°C).

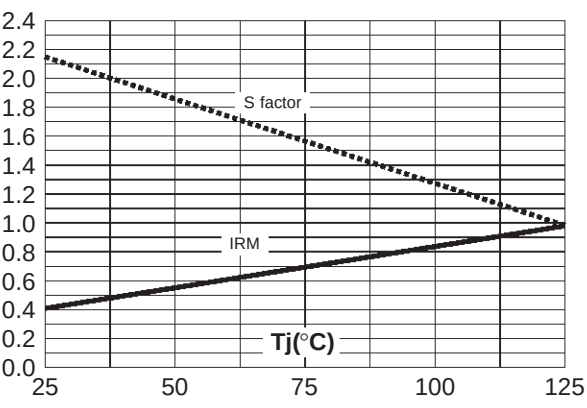


Fig. 8: Transient peak forward voltage versus dI_F/dt (90% confidence, per diode).

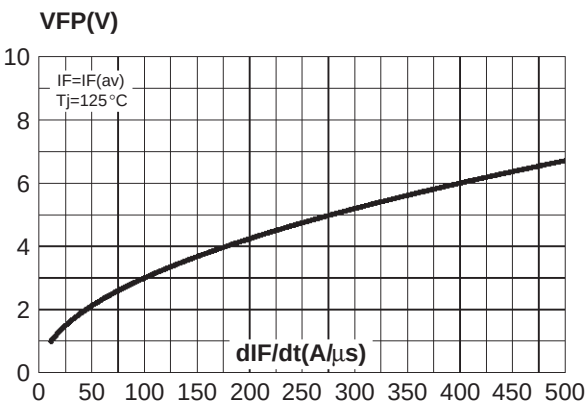
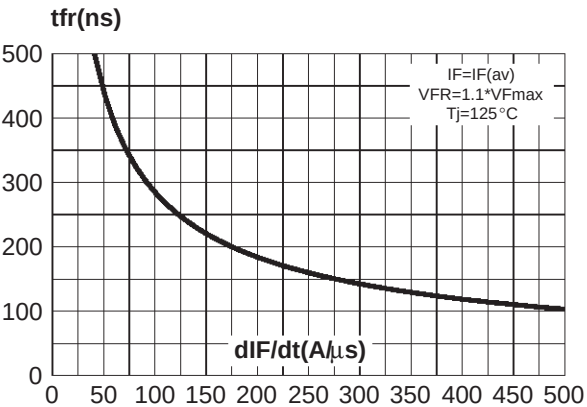


Fig. 9: Forward recovery time versus dI_F/dt (90% confidence, per diode).



PACKAGE MECHANICAL DATA
ISOTOP

REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	11.80	12.20	0.465	0.480
A1	8.90	9.10	0.350	0.358
B	7.8	8.20	0.307	0.323
C	0.75	0.85	0.030	0.033
C2	1.95	2.05	0.077	0.081
D	37.80	38.20	1.488	1.504
D1	31.50	31.70	1.240	1.248
E	25.15	25.50	0.990	1.004
E1	23.85	24.15	0.939	0.951
E2	24.80 typ.		0.976 typ.	
G	14.90	15.10	0.587	0.594
G1	12.60	12.80	0.496	0.504
G2	3.50	4.30	0.138	0.169
F	4.10	4.30	0.161	0.169
F1	4.60	5.00	0.181	0.197
P	4.00	4.30	0.157	0.69
P1	4.00	4.40	0.157	0.173
S	30.10	30.30	1.185	1.193

PACKAGE MECHANICAL DATA
 TO-247

REF.	DIMENSIONS					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.85		5.15	0.191		0.203
D	2.20		2.60	0.086		0.102
E	0.40		0.80	0.015		0.031
F	1.00		1.40	0.039		0.055
F1		3.00			0.118	
F2		2.00			0.078	
F3	2.00		2.40	0.078		0.094
F4	3.00		3.40	0.118		0.133
G		10.90			0.429	
H	15.45		15.75	0.608		0.620
L	19.85		20.15	0.781		0.793
L1	3.70		4.30	0.145		0.169
L2		18.50			0.728	
L3	14.20		14.80	0.559		0.582
L4		34.60			1.362	
L5		5.50			0.216	
M	2.00		3.00	0.078		0.118
V		5°			5°	
V2		60°			60°	
Dia.	3.55		3.65	0.139		0.143

Ordering code	Marking	Package	Weight	Base qty	Delivery mode
STTH6006TV1	STTH6006TV	ISOTOP	27g without screws	10 with screws	Tube
STTH6006CW	STTH6006CW	TO-247	4.36g	30	Tube

- Cooling method: by conduction (C)
- Recommended torque value (ISOTOP): 1.3 N.m.
- Recommended torque value (TO-247°): 0.8 N.m.
- Maximum torque value (ISOTOP): 1.5 N.m.
- Maximum torque value (TO-247): 1.0 N.m.
- Epoxy meets UL 94, V0

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